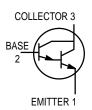
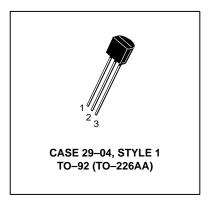
# **High Voltage Darlington Transistors NPN Silicon**

BC372 BC373





#### **MAXIMUM RATINGS**

Rating	Symbol	BC372	BC373	Unit		
Collector-Emitter Voltage	V <sub>CES</sub>	100	80	Vdc		
Collector-Base Voltage	VCBO	100	80	Vdc		
Emitter-Base Voltage	V <sub>EBO</sub>	12		Vdc		
Collector Current — Continuous	IC	1.0		Adc		
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C		
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12				Watt mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C		

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta}JA$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta}JC$	83.3	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteris	tic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 100 μAdc, I <sub>B</sub> = 0)	BC372 BC373	V(BR)CES	100 80	_	_	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	BC372 BC373	V(BR)CBO	100 80		_	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V(BR)EBO	12	_	_	Vdc
Collector Cutoff Current $(V_{CB} = 80 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_{E} = 0)$	BC372 BC373	ІСВО	_	_	100 100	nAdc
Emitter Cutoff Current (VEB = 10 V, I <sub>C</sub> = 0)		IEBO	_	_	100	nAdc

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle 2.0%.



# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Chanastanistia	Compleal	Min	T	Mari	11
Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain (I <sub>C</sub> = 250 mAdc, V <sub>CF</sub> = 5.0 Vdc)	hFE	8.0	_	_	К
$(I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$		10	_	160	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 250 mAdc, I <sub>B</sub> = 0.25 mAdc)	VCE(sat)	_	1.0	1.1	Vdc
Base-Emitter Saturation Voltage (I <sub>C</sub> = 250 mAdc, I <sub>B</sub> = 0.25 mAdc)	V <sub>BE(sat)</sub>	_	1.4	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain Bandwidth Product (IC = 100 mAdc, VCE = 5.0 Vdc, f = 100 MHz)	fT	100	200	_	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C <sub>ob</sub>	_	10	25	pF
Noise Figure (I <sub>C</sub> = 1.0 mAdc, $V_{CE}$ = 5.0 Vdc, $R_g$ = 100 k ohm, f = 1.0 kHz)	NF	_	2.0	_	dB

<sup>1.</sup> Pulse Test: Pulse Width =  $300 \mu s$ , Duty Cycle 2.0%.

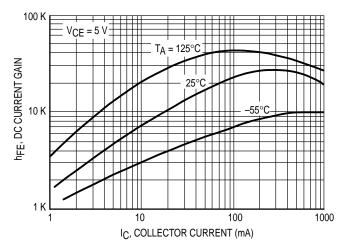


Figure 1. DC Current Gain

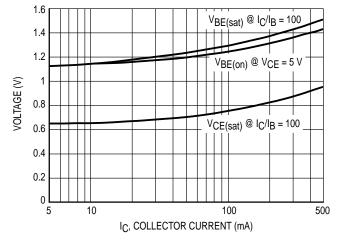


Figure 2. "Saturation" and "On" Voltages

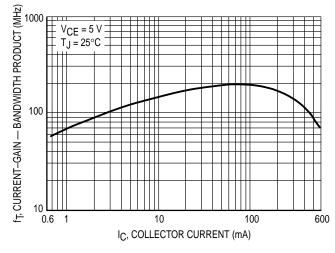


Figure 3. Current-Gain — Bandwidth Product

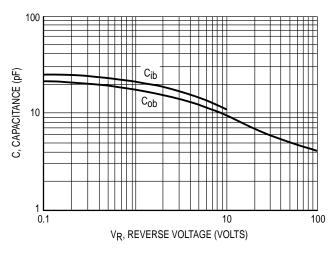
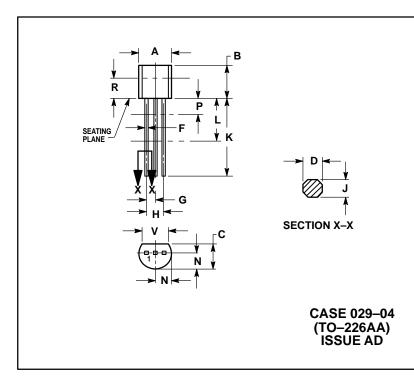


Figure 4. Capacitances

## **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	

STYLE 1: PIN 1. EMITTER

2. BASE 3. COLLECTOR

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